

# PSMN8R7-100YSF

# NextPower 100 V, 9 m $\Omega$ N-channel MOSFET in LFPAK56 package

1 November 2017

**Product data sheet** 

## 1. General description

NextPower 100 V standard level gate drive MOSFET. Qualified to 175 °C and recommended for industrial & consumer applications.

#### 2. Features and benefits

- · Low Q<sub>rr</sub> for higher efficiency and lower spiking
- Qualified to 175 °C
- Low Q<sub>G</sub> x R<sub>DSon</sub> FOM for high efficiency switching applications
- Strong avalanche energy rating (E<sub>as</sub>)
- Avalanche rated and 100% tested
- Ha-free and RoHS compliant LFPAK56 package
- Wave-solderable LFPAK56 package

## 3. Applications

- Synchronous rectifier in AC-DC and DC-DC
- · BLDC motor control
- USB-PD and mobile fast-charge adapters
- · LED lighting
- Full-bridge and half-bridge applications
- Flyback and resonant topologies

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-	100	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	-	90	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	-	198	W
Tj	junction temperature		-55	-	175	°C
Static chara	acteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 10	-	7.2	9	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 100 °C; Fig. 11	-	10.7	14	mΩ
Dynamic ch	naracteristics					
$Q_{GD}$	gate-drain charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V;	-	7.5	-	nC
Q <sub>G(tot)</sub>	total gate charge	Fig. 12; Fig. 13	-	38.5	-	nC



Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche ruggedness							
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 30.3 A; $V_{sup} \le 100$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; Fig. 4; Unclamped	[1]	-	-	234	mJ
Source-drain diode							
Q <sub>r</sub>	recovered charge	$I_S$ = 25 A; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 50 V; Fig. 16		_	52.6	-	nC

<sup>[1]</sup> Protected by 100% test

## 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G P
4	G	gate		mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package				
	Name	Description	Version		
PSMN8R7-100YSF	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PSMN8R7-100YSF	8F7S10

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	100	V
$V_{DGR}$	drain-gate voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ		-	100	V
$V_{GS}$	gate-source voltage			-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	198	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	90	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>		-	71	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$ ; Fig. 3		-	360	Α
T <sub>stg</sub>	storage temperature			-55	175	°C
T <sub>j</sub>	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-drai	n diode	1				
Is	source current	T <sub>mb</sub> = 25 °C		-	90	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	360	Α
Avalanche r	uggedness				'	
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 30.3 A; $V_{sup} \le$ 100 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; Fig. 4; Unclamped	[1]	-	234	mJ
I <sub>AS</sub>	non-repetitive avalanche current	$V_{sup} \le 100 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $R_{GS} = 50 \Omega$	[1]	-	30.3	Α

<sup>[1]</sup> Protected by 100% test

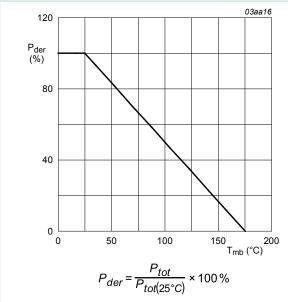


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

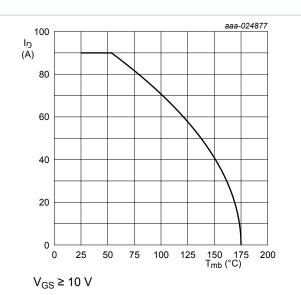
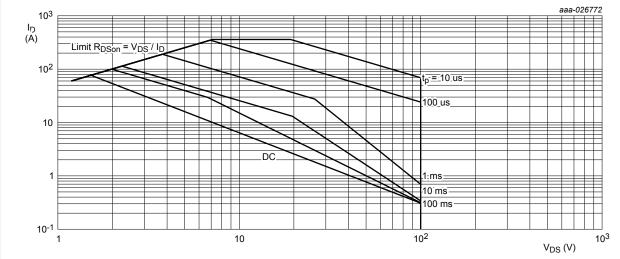
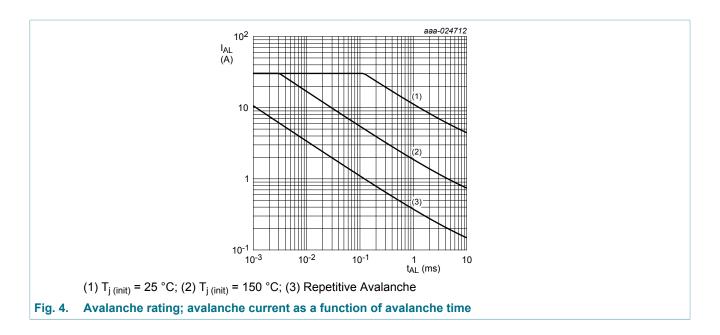


Fig. 2. Continuous drain current as a function of mounting base temperature



T<sub>mb</sub> = 25 °C; I<sub>DM</sub> is a single pulse

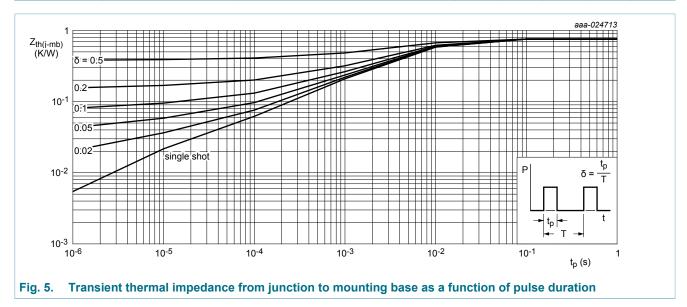
Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	0.67	0.76	K/W



#### 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	100	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	90	-	-	V
V <sub>GS(th)</sub>	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	3.6	-	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	-	1.9	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 9$	2	3.1	4	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-8	-	mV/K
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.02	5	μA
		V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	-	100	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	5	100	nA
		V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	5	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_{D}$ = 25 A; $T_{j}$ = 25 °C; Fig. 10	-	7.2	9	mΩ
		V <sub>GS</sub> = 7 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	8.2	13.2	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 100 °C; Fig. 11	-	10.7	14	mΩ
		$V_{GS}$ = 10 V; $I_{D}$ = 25 A; $T_{j}$ = 175 °C; Fig. 11	-	15.8	19.8	mΩ
$R_G$	gate resistance	f = 1 MHz	-	0.8	-	Ω
Dynamic cha	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; Fig. 12; Fig. 13	-	38.5	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	19.8	-	nC
$Q_GS$	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$	-	12.8	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	Fig. 12; Fig. 13	-	7.7	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	5.1	-	nC
$Q_GD$	gate-drain charge		-	7.5	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; <u>Fig. 12</u> ; <u>Fig. 13</u>	-	4.9	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	2758	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 14</u>	-	532	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	17	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 2 \Omega; V_{GS} = 10 \text{ V};$	-	12.5	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	11	_	ns

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$t_{d(off)}$	turn-off delay time			-	22.5	-	ns
t <sub>f</sub>	fall time			-	12.7	-	ns
Source-drain	Source-drain diode						
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 15$		-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	45.5	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 50 V; <u>Fig. 16</u>		-	52.6	-	nC

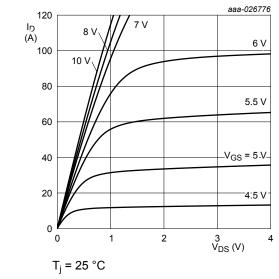


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

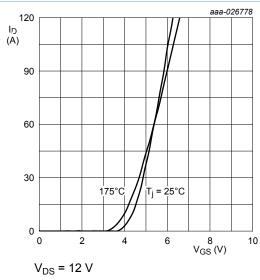


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

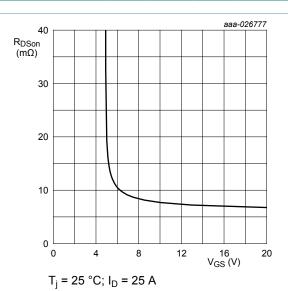


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

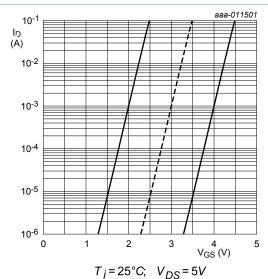


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

10  $V_{GS}$ 

8

6

2

0

10

 $T_i = 25 \,^{\circ}C; I_D = 25 \,^{\circ}A$ 

aaa-026779

120 150 T<sub>j</sub> (°C)

180

#### NextPower 100 V, 9 mΩ N-channel MOSFET in LFPAK56 package

2

1.6

1.2

0.8

0.4

-60 -30 0

30

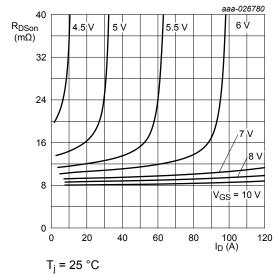


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

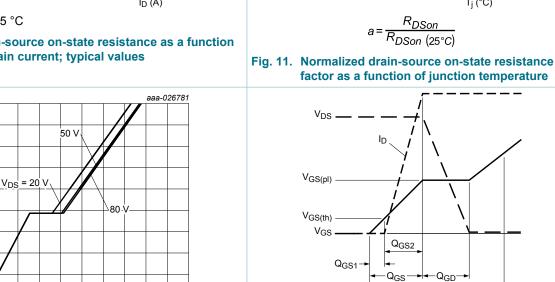


Fig. 12. Gate-source voltage as a function of gate charge; typical values

20

30

40 Q<sub>G</sub> (nC)

50



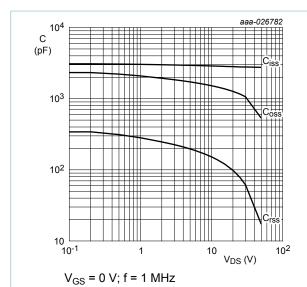
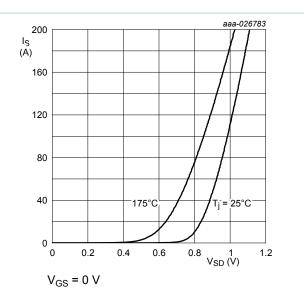


Fig. 14. Input, output and reverse transfer capacitances | Fig. 15. Source-drain (diode forward) current as a as a function of drain-source voltage; typical values



function of source-drain (diode forward) voltage; typical values

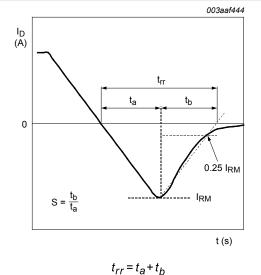
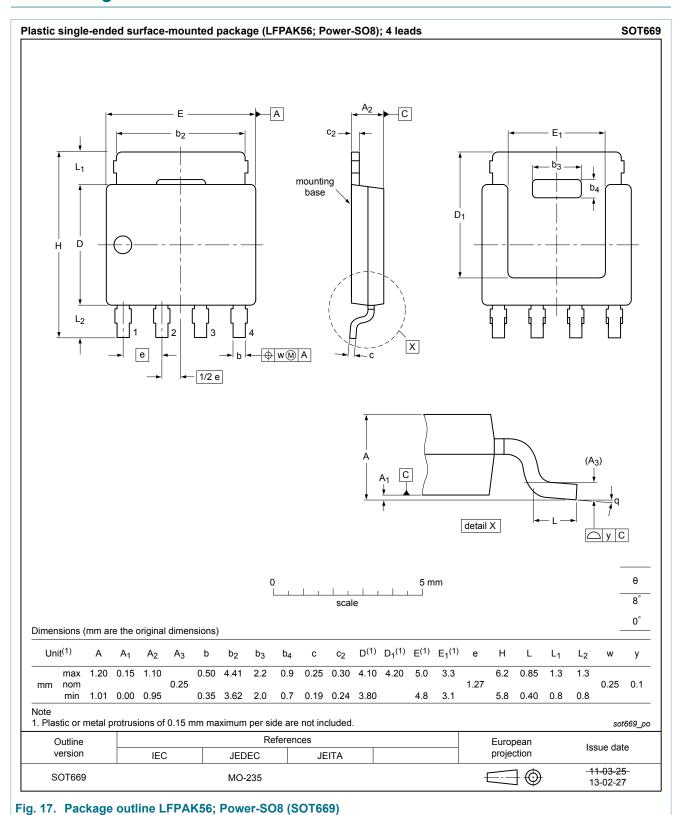
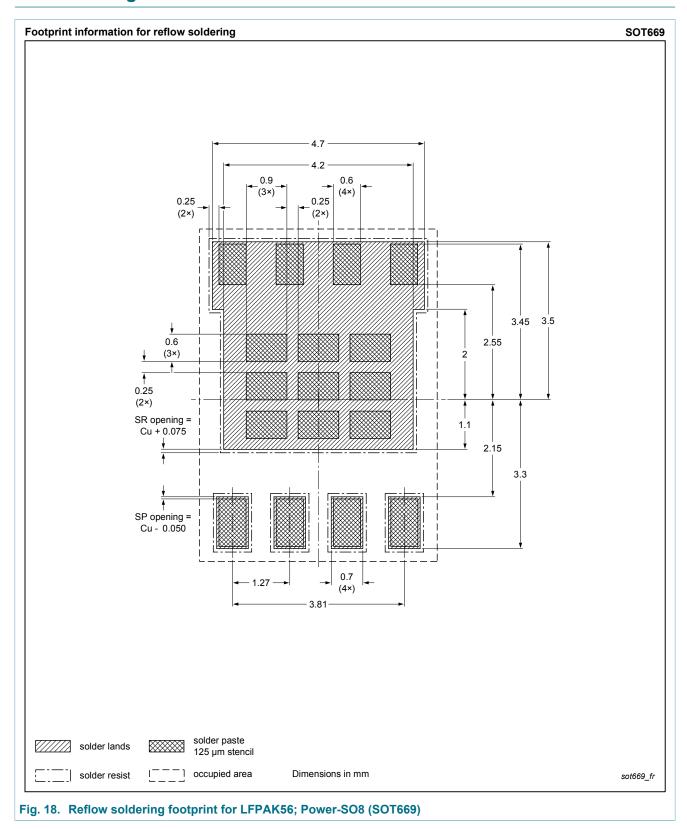


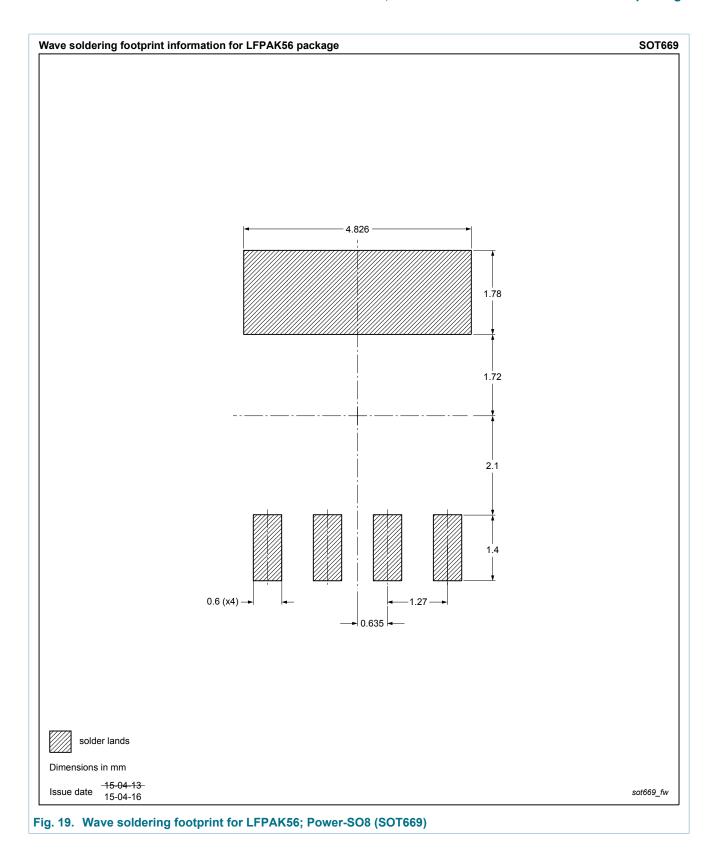
Fig. 16. Reverse recovery waveform definitions

## 11. Package outline



## 12. Soldering





# 13. Legal information

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